



**浩畅半导体**  
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**2SA1235 PNP Transistors**

**SOT-23 Plastic-Encapsulate Transistors**

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客户确认：

公司签章：

部门

工程部

品保部

采购部

签名

日期

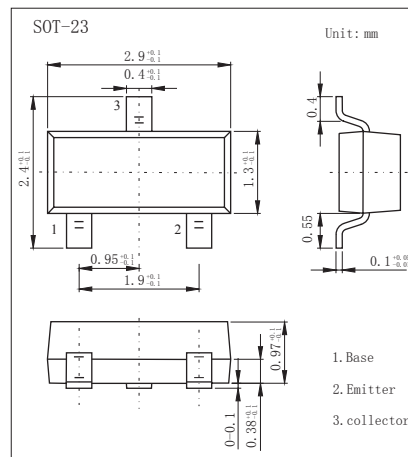


**SOT-23 Plastic-Encapsulate Transistors**

**2SA1235 PNP Transistors**

■ Features

- Small collector to emitter saturation voltage.
- Excellent lineary DC forward current gain.
- Super mini package for easy mounting.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EB0</sub>	-6	V
Collector current	I <sub>c</sub>	-200	mA
Collector dissipation (Ta=25°C)	P <sub>c</sub>	200	mW
Jumction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

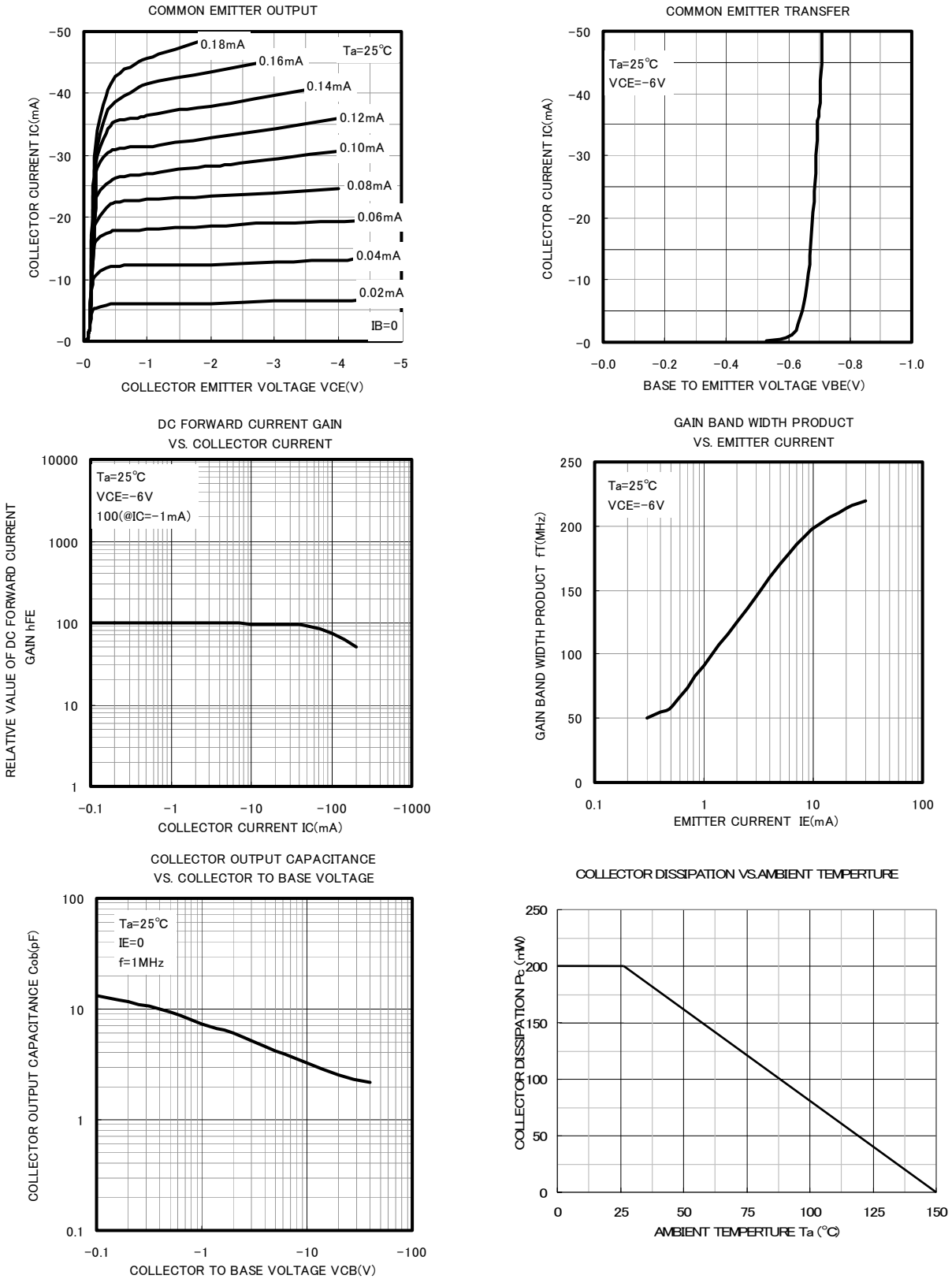
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = -100 μA, I <sub>E</sub> =0	-50			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>c</sub> = -1 mA, I <sub>B</sub> =0	-50			
Emitter - base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = -100 μA, I <sub>c</sub> =0	-6			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -50 V, I <sub>E</sub> =0			-0.1	uA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = -6V, I <sub>c</sub> =0			-0.1	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =-100 mA, I <sub>B</sub> =-10mA			-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> =-100 mA, I <sub>B</sub> =-10mA			-1.2	
DC forward current gain	h <sub>FE</sub>	V <sub>CE</sub> = -6V, I <sub>c</sub> = -1mA	150		800	
		V <sub>CE</sub> = -6V, I <sub>c</sub> = -0.1mA	90			
Noise figure	NF	V <sub>CB</sub> = -6V, I <sub>E</sub> = 0.3mA, f=100 Hz, R <sub>G</sub> =10kΩ			20	dB
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -6V, I <sub>E</sub> = 0, f=1MHz		4		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -6V, I <sub>E</sub> = -10mA		200		MHz

■ Classification of h<sub>FE</sub>(1)

Type	2SA1235-E	2SA1235-F	2SA1235-G
Range	150-300	250-500	400-800
Marking	ME	MF	MG

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## Typical Characteristics



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## ■ Typical Characteristics

